

DAN217U / BAV99U / DAN217

Diodes

Switching diode

DAN217U / BAV99U *1 / DAN217

*1 BAV99U is only sold in countries other than Japan.

●Application

Ultra high speed switching

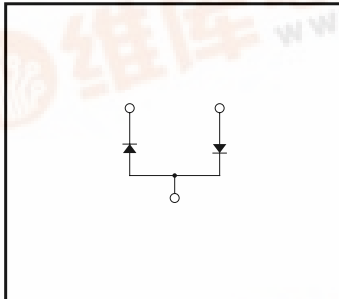
●Features

- 1) Small surface mounting type. (UMD3,SMD3)
- 2) Two diode elements are connected in series (V_F × 2) per circuit.

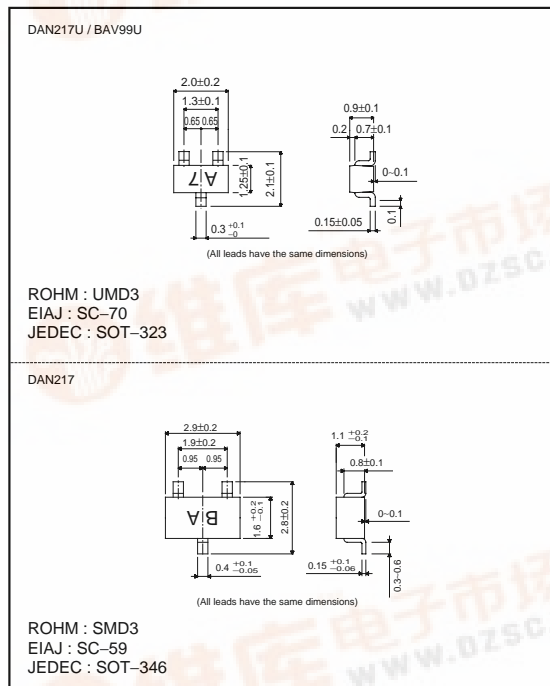
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Type	Peak reverse voltage V _{RM} (V)	DC reverse voltage V _R (V)	Peak forward current I _{FM} (mA)	Mean rectifying current I _o (mA)	Surge current (1μs) I _{surge} (mA)	Power dissipation (TOTAL) Pd(mW)	Junction temperature T _j (°C)	Storage temperature T _{stg} (°C)
DAN217U	80	80	300	100	4000	200	150	-55 ~ +150
BAV99U	80	80	300	100	4000	200	150	-55 ~ +150
DAN217	80	80	300	100	4000	200	150	-55 ~ +150

Diodes

●Electrical characteristics (Ta=25°C)

Type	Forward voltage		Reverse current		Fig
	V _F (V) Max.	Cond. I _F (mA)	I _R (μA) Max.	Cond. V _R (V)	
DAN217U	1.2	100	0.2	70	1 ~ 3
BAV99U	1.2	100	0.2	70	1 ~ 3
DAN217	1.2	100	0.1	70	4 ~ 6

●Electrical characteristic curves (Ta=25°C)
(DAN217U,BAV99U)···Fig.1~3

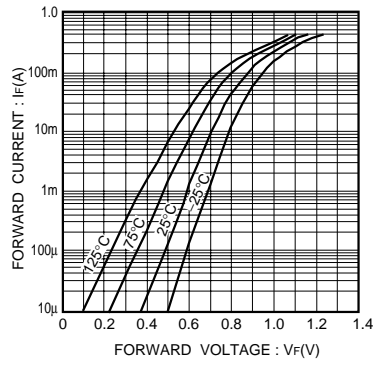


Fig.1 Forward characteristics

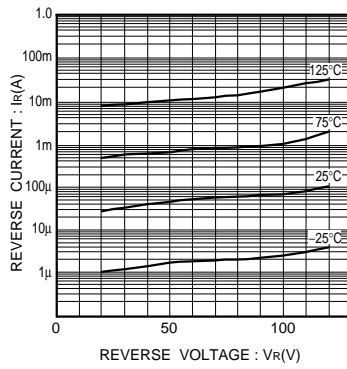


Fig.2 Reverse characteristics

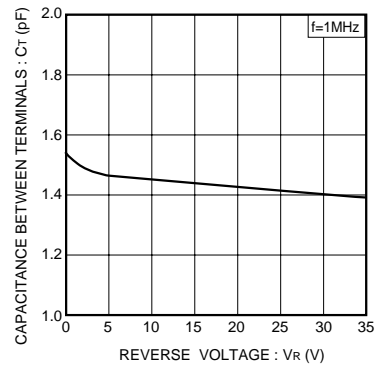


Fig.3 Capacitance between terminals characteristics

(DAN217) ···Fig.4~6

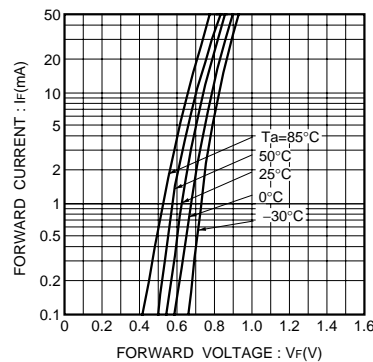


Fig.4 Forward characteristics

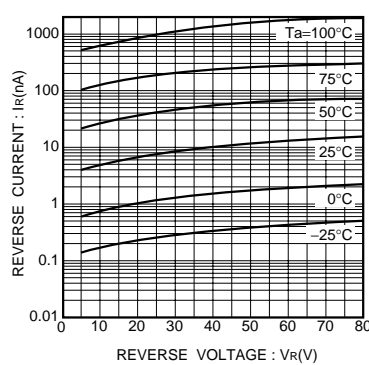


Fig.5 Reverse characteristics

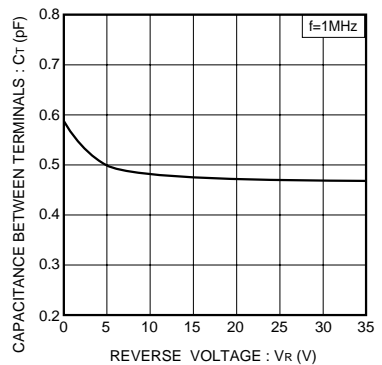


Fig.6 Capacitance between terminals characteristics